INA5001AC1

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE

DESCRIPTION

INA5001AC1 is a super mini package resin sealed silicon PNP epitaxial transistor.

It is designed for relay drive or Power supply application.

FEATURE

- •Super mini package for easy mounting
- Low $V_{CE(sat)} = V_{CE(sat)} = -0.5 V_{max}$ (@I_C=-500mA/I_B=-50mA)
- High collector current $I_c=-1A$
- ●High voltage V_{CEO}=-50V

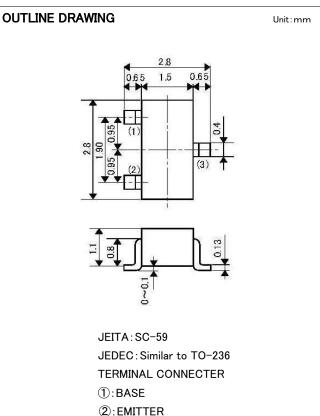
APPLICATION

Relay drive, Power supply for audio equipment, VTR , etc

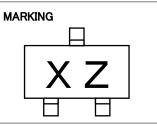
MAXIMUM RATINGS(Ta=25°C)

Symbol	Parameter	Ratings	Unit	
V_{CBO}	Collector to Base voltage	-50	V	
V _{EBO}	Emitter to Base voltage	-5	V	
V _{CEO}	Collector to Emitter voltage	-50	V	
I _c	Collector current	-1	А	
I _{CM}	Peak collector current	-2	А	
Pc	Collector dissipation	200	mW	
T _j	Junction temperature	+150	°C	
T_{stg}	Storage temperature	-55 ~ +150	°C	

ELECTRICAL CHARACTERISTICS(Ta=25°C)



- 3:COLLECTOR



Symbol	Parameter	Test conditions	Limits			Unit
			Min	Тур	Max	Unit
V _{(BR)CBO}	C to B break down voltage	I _c =-10μA, I _E =0	-50	-	-	V
V _{(BR)EBO}	E to B break down voltage	I_{E} =-10µA, I_{C} =0	-5	-	-	V
V _{(BR)CEO}	C to E break down voltage	I_{c} =-1mA, R_{BE} =∞	-50	-	_	V
I _{CBO}	Collector cut off current	V_{CB} =-50V, I _E =0mA	-	-	-0.1	μA
I _{EBO}	Emitter cut off current	V _{EB} =-5V, I _C =0mA	-	-	-0.1	μA
h_{FE}	DC forward current gain	$V_{CE} = -4V, I_{C} = -0.1A$	160	_	380	
$V_{\text{CE(sat)}}$	C to E Saturation Voltage	I _c =-500mA, I _B =-50mA	-	-	-0.5	V
f _T	Gain bandwidth product	V _{CE} =-2V, I _E =500mA	_	120	-	MHz
C _{ob}	Collector output capacitance	V_{CB} =-10V, I _E =0mA, f=1MHz	_	12	-	pF

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COMMON EMITTER OUTPUT Collector dissipation-AMBIENT TEMPERATURE -5 0mA -0.6 500 4.5mA PcMAX=0.2W Ta=25°C -4.0mA -3.5mA -3.0mA (Mm) 400 ₹ Ъс _ -2.5mA Ŋ -0.4**Collector dissipation Collector** current -2.0mA 300 5m/ 200 -1mA -0.2 IB=-0.5mA 100 0 -0 0 40 120 160 200 80 -0 -3 -1-2 AMBIENT TEMPERATURE Ta (°C) COLLECTOR TO EMITTER VOLTAGE VCE (V) DC forward current gain VS. Collector current COMMON EMITTER TRANSFER -100 1000 VCE=-4V VCE=-4V Collector current IC(mA) DC forward current gain hFE Ta=85℃ -10 25°C Ta=85°C -40°C 100 25°C -40°C -1 10 -0.1 -1 -10 -100-1000 -0 -0.2 -0.4 -0.6 -0.8 -1 -1.2 -0.1 BASE TO EMITTER VOLTAGE VBE (V) Collector current IC(mA) COLLECTOR TO EMITTER SATURATION VOLTAGE COLLECTOR TO EMITTER SATURATION VOLTAGE VS. BASE CURRENT VS. COLLECTOR CURRENT -1.6 -1000 Ta=25°C IC/IB=10 COLLECTOR TO EMITTER SATURATION VOLTAGE VCE (V) -1.4 COLLECTOR TO EMITTER SATURATION -1.2 VOLTAGE VCE(sat) (mV) -1 -0.2A -0.3A IC=-0.1A 0.4A 100 -0.8 Ta=85°C -0.6 25°C -0.4 -0.2 -40°C -10 -0 -0.1 -1 -10 -100 -1000 -0.1 -100 -1 -10 COLLECTOR CURRENT IC(mA) BASE CURRENT IB (mA)

TYPICAL CHARACTERISTICS

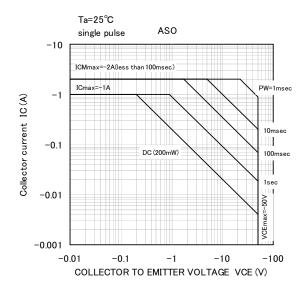
ISAHAYA ELECTRONICS CORPORATION

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GAIN BAND WIDTH PRODUCT COLLECTOR OUTPUT CAPACITANCE VS. EMITTER CURRENT VS. COLLECTOR TO BASE VOLTAGE 1000 100 Ta=25℃ Ta=25°C VCE=-2V COLLECTOR OUTPUT CAPACITANCE IE=0 GAIN BAND WIDTH PRODUCT FT (MHz) f=1MHz 100 Cob (pF) 10 10 1 1 1000 10 100 -10 -100 0.1 1 -0.1-1 EMITTER CURRENT IE (mA) COLLECTOR TO BASE VOLTAGE VCB (V)

TYPICAL CHARACTERISTICS





6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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